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## PATENT ABSTRACTS OF JAPAN

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**H01L 29/784**(21) Application number: **03271504**(71) Applicant: **FUJITSU LTD**(22) Date of filing: **18.10.91**(72) Inventor: **SUZUKI KUNIHIRO**(54) **MANUFACTURE OF SEMICONDUCTOR DEVICE**

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(57) Abstract:

**PURPOSE:** To provide a method of manufacturing an insulated gate type FET, where the insulated gate type FET is prevented from varying in threshold value due to the penetration of boron (B) into a substrate by using a gate oxide film when boron fluoride ( $\text{BF}_2$ ) ions are implanted for the formation of a shallow source-drain junction.

**CONSTITUTION:** A first process where a thermally oxidized gate oxide film 2 is formed on the surface of an N-type silicon substrate 1 and a polysilicon film 3 is grown thereon, a second process where B ions are implanted into the polysilicon film 3, a third process where an implantation mask 4 is laid on the polysilicon film 3, and the polysilicon film 3 and the implantation mask 4 are patterned and left on a gate forming region, and a fourth process where  $\text{BF}_2$  ions are implanted into the substrate 1 using the patterned implantation mask 4 as a mask, and the substrate 1 is thermally treated to form a source/ drain region 1A are provided.

